### DISCRETE SEMICONDUCTORS

# DATA SHEET

**PEMB10**; **PUMB10** PNP/PNP resistor-equipped transistors; R1 = 2.2 kΩ, R2 = 47 kΩ

Product specification Supersedes data of 2001 Sep 14 2003 Oct 03





 $\mathsf{k}\Omega$ 

# PNP/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

PEMB10; PUMB10

#### **FEATURES**

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral drivers
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
TR1	PNP	_	_	-
TR2	PNP	_	_	_
R1	bias resistor	2.2	_	kΩ

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**QUICK REFERENCE DATA** 

bias resistor

#### **DESCRIPTION**

PNP/PNP resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACKAGE		MARKING CODE(1)	NPN/PNP	NPN/NPN
I TPE NOWIBER	PHILIPS	EIAJ	MARKING CODE	COMPLEMENT	COMPLEMENT
PEMB10	SOT666	_	Z5	PEMD10	PEMH10
PUMB10	SOT363	SC-88	B*0	PUMD10	PUMH10

R2

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING		
TIPE NUMBER	SIMIFLIFIED OUTLINE AND STRIBOL	PIN	DESCRIPTION	
PEMB10	6 5 4	1	emitter TR1	
PUMB10	6 5 4	2	base TR1	
	R1 R2	3	collector TR2	
	TR2	4	emitter TR2	
	TR1	5	base TR2	
		6	collector TR1	
	1 2 3 Top view MAM477			
	1 OP VIEW INAINA//			

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### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
I TPE NOWIBER	NAME	DESCRIPTION	VERSION
PEMB10	_	plastic surface mounted package; 6 leads	SOT666
PUMB10	_	plastic surface mounted package; 6 leads	SOT363

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT			
Per transistor								
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V			
V <sub>CEO</sub>	collector-emitter voltage	open base	_	-50	V			
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-10	V			
VI	input voltage							
	positive		_	+5	V			
	negative		_	-12	V			
Io	output current (DC)		_	-100	mA			
I <sub>CM</sub>	peak collector current	k collector current –		-100	mA			
P <sub>tot</sub>	total power dissipation	al power dissipation T <sub>amb</sub> ≤ 25 °C						
	SOT363	note 1	-	200	mW			
	SOT666	notes 1 and 2	_	200	mW			
T <sub>stg</sub>	storage temperature		-65	+150	°C			
Tj	junction temperature		_	150	°C			
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C			
Per device	•	•	·	•				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C						
	SOT363	note 1	_	300	mW			
	SOT666	notes 1 and 2	_	300	mW			

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

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#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th j-a</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	note 1	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	_	_	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-180	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}$	100	_	_	
V <sub>CEsat</sub>	saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	_	_	-100	mV
$V_{i(off)}$	input-off voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	_	-0.6	-0.5	V
V <sub>i(on)</sub>	input-on voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-1.1	-0.75	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
R2 R1	resistor ratio		17	21	26	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	_	3	pF

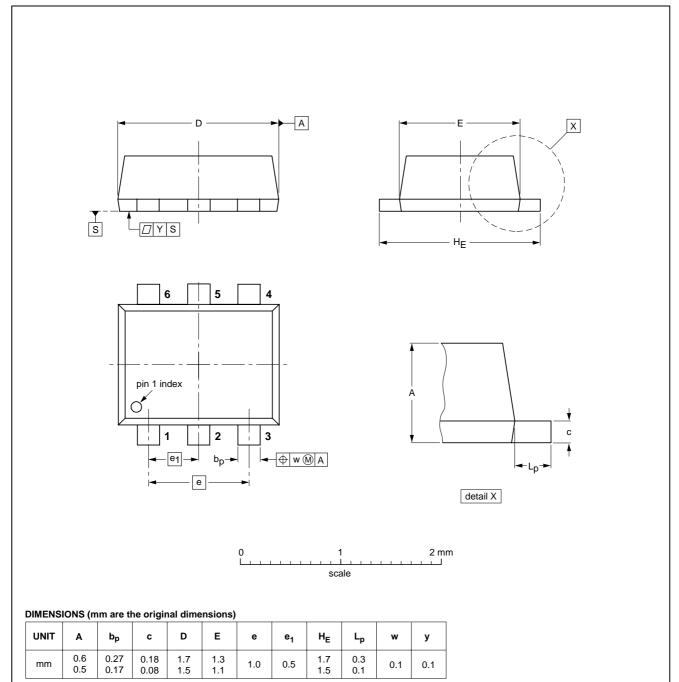
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### **PACKAGE OUTLINES**

Plastic surface mounted package; 6 leads

SOT666



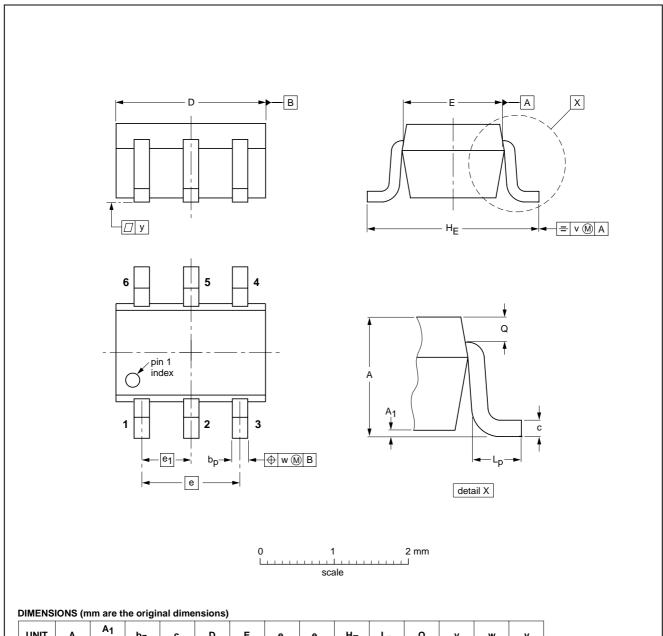
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT666						<del>-01-01-04</del> 01-08-27	

# PNP/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 47 k $\Omega$

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### Plastic surface mounted package; 6 leads

**SOT363** 



UN	IIT	Α	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	٧	w	у
m	m	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT363			SC-88			97-02-28

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#### **DATA SHEET STATUS**

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### **DEFINITIONS**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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#### **Contact information**

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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